



TM020H03S

N+N-Channel Enhancement Mode Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

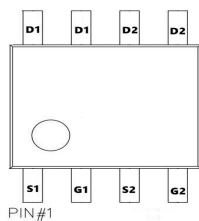
Product Summary

$V_{DS} = 30V$ $I_D = 6.8A$

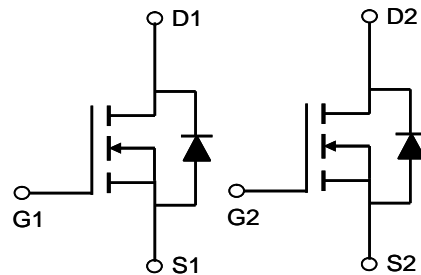
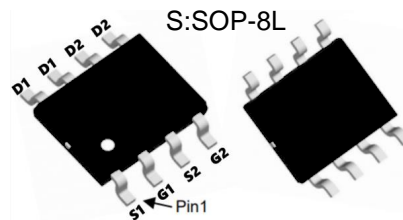
$R_{DS(ON)} = 20m\Omega$ (typ.) @ $V_{GS} = 10V$

100% UIS Tested

100% R_g Tested



Marking: 4812



Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6.0	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.2	A
I_{DM}	Pulsed Drain Current ²	23.4	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	---	$^\circ C/W$

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.7	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	$V_{GS}=10V, I_D=5.5A$	-	20	32	m Ω
		$V_{GS}=4.5V, I_D=4.5A$	-	28	37	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0\text{MHz}$	-	490	-	pF
C_{oss}	Output Capacitance		-	79	-	pF
C_{rss}	Reverse Transfer Capacitance		-	61	-	pF
Q_g	Total Gate Charge	$V_{DS}=15V, I_D=5.8A,$ $V_{GS}=10V$	-	5.2	-	nC
Q_{gs}	Gate-Source Charge		-	0.9	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	1.3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V,$ $I_D=3A, R_{GEN}=3\Omega,$ $V_{GS}=10V$	-	4.5	-	ns
t_r	Turn-on Rise Time		-	2.5	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	14.5	-	ns
t_f	Turn-off Fall Time		-	3.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	6.8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	23.2	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=5.8A$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

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Figure 1: Output Characteristics

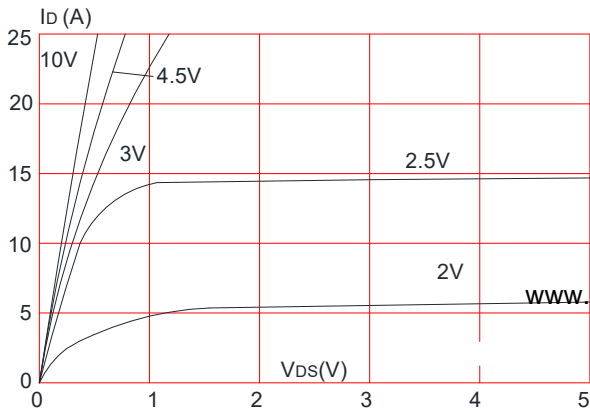


Figure 2: Typical Transfer Characteristics

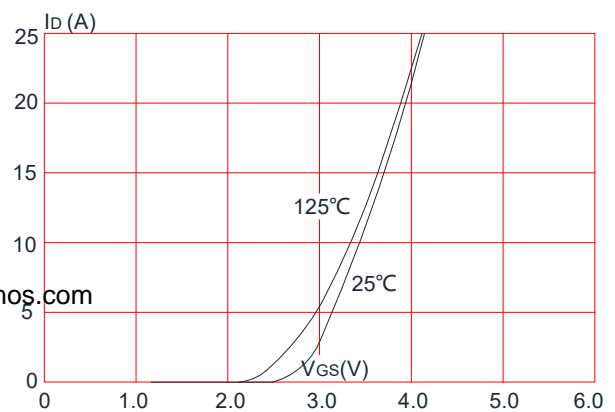


Figure 3: On-resistance vs. Drain Current

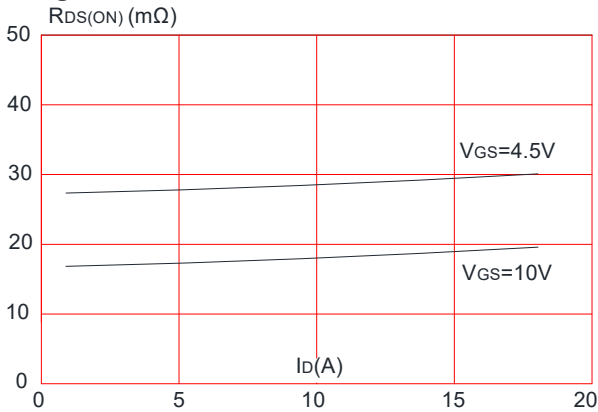


Figure 4: Body Diode Characteristics

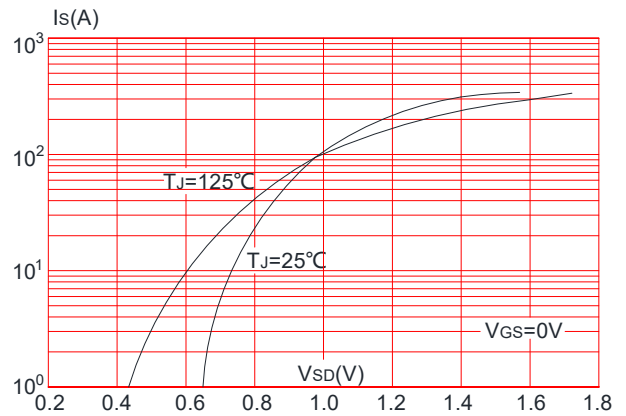


Figure 5: Gate Charge Characteristics

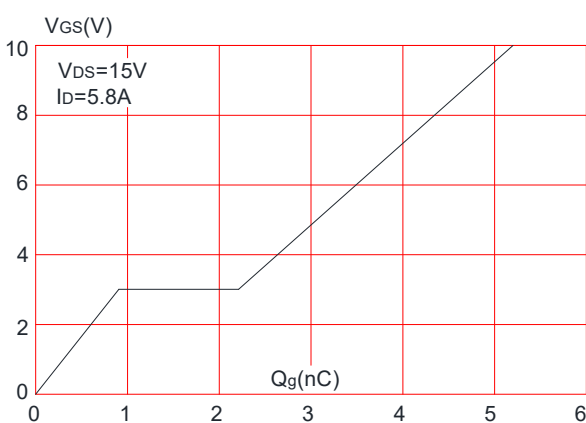
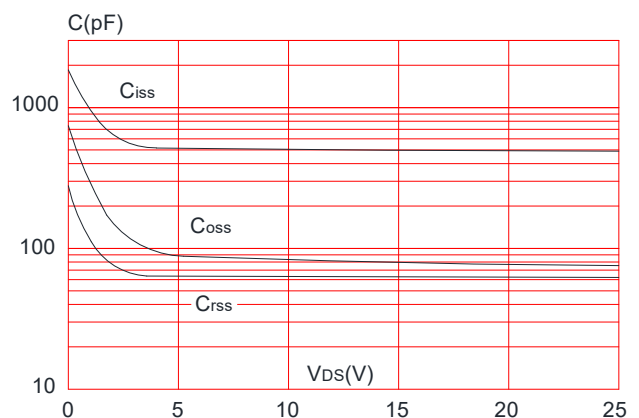


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

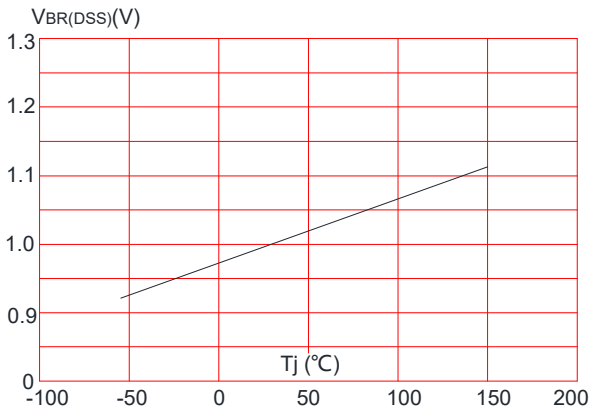


Figure 8: Normalized on Resistance vs. Junction Temperature

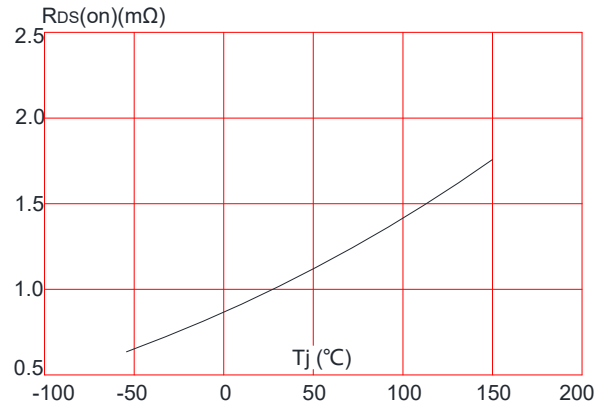


Figure 9: Maximum Safe Operating Area

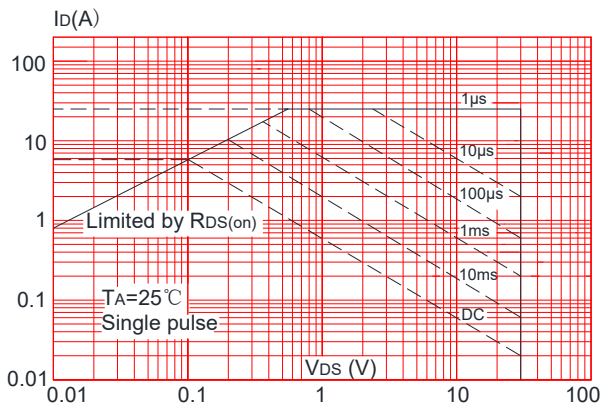


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

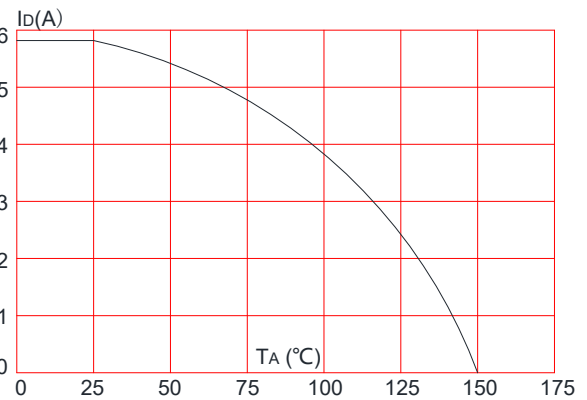
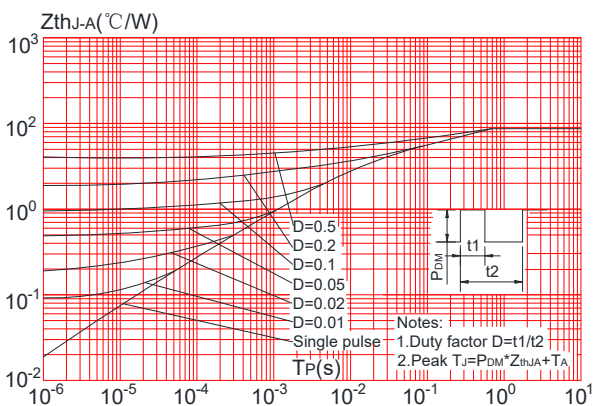
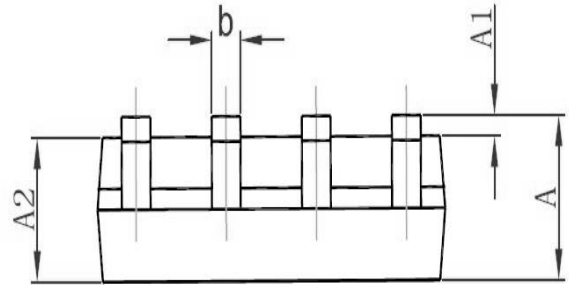
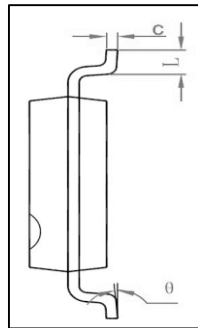
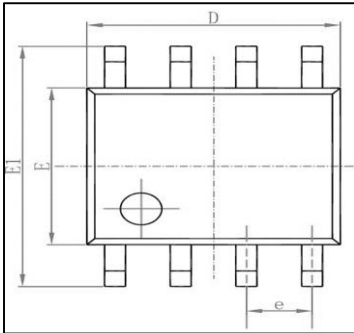


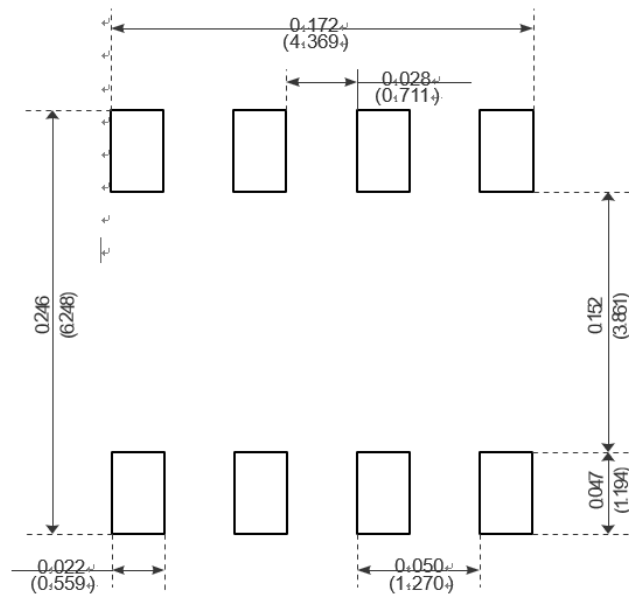
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



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